

ABSTRACT

A method for fabricating a metal-insulator-metal capacitor in an embedded DRAM process is described. A plurality of contact plugs are provided through an insulating layer to semiconductor device structures in a substrate wherein the contact plugs are formed in a logic area of the substrate and in a memory area of the substrate and providing node contact plugs to node contact regions within the substrate in the memory area. Thereafter, capacitors are fabricated in a twisted trench in a self-aligned copper process.